

# Qingyun Xie

## List of Publications by Year in descending order

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Version: 2024-02-01

10  
papers

365  
citations

1478505

6  
h-index

1872680

6  
g-index

10  
all docs

10  
docs citations

10  
times ranked

279  
citing authors

#	ARTICLE	IF	CITATIONS
1	Self-Aligned E-Mode GaN <i>p</i> -Channel FinFET With $I_{ON} > 100$ mA/mm and $I_{ON}/I_{OFF} > 10^4$ . IEEE Electron Device Letters, 2022, 43, 358-361.	3.9	22
2	Tungsten-Gated GaN/AlGaN <i>p</i> -FET With $I_{max} > 120$ mA/mm on GaN-on-Si. IEEE Electron Device Letters, 2022, 43, 545-548.	3.9	19
3	Performance Estimation of GaN CMOS Technology. , 2021, , .		4
4	Emerging GaN technologies for power, RF, digital, and quantum computing applications: Recent advances and prospects. Journal of Applied Physics, 2021, 130, .	2.5	89
5	Regrowth-Free GaN-Based Complementary Logic on a Si Substrate. IEEE Electron Device Letters, 2020, 41, 820-823.	3.9	74
6	Field-induced Acceptor Ionization in Enhancement-mode GaN p-MOSFETs. , 2020, , .		19
7	<i>p</i> -Channel GaN Transistor Based on <i>p</i> -GaN/AlGaN/GaN on Si. IEEE Electron Device Letters, 2019, 40, 1036-1039.	3.9	88
8	First Demonstration of a Self-Aligned GaN p-FET. , 2019, , .		25
9	A passively temperature-compensated dual-frequency AlN-on-silicon resonator for accurate pressure sensing. , 2017, , .		10
10	Effectiveness of oxide trench array as a passive temperature compensation structure in AlN-on-silicon micromechanical resonators. Applied Physics Letters, 2017, 110, .	3.3	15